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Bezeichnung der Erfindung/Title of the invention/Titre de l'invention:
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Method of producing semiconductor elements using a test structure

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Method of producing semiconductor elements using a test structure

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(68)

The present invention relates to a testing of the production of at least one semiconductor element in a semiconductor substrate.

5 United States patent 6,054,721 discloses a method of producing semiconductor elements on a semiconductor wafer using a predetermined test structure that is produced on the same semiconductor wafer during the fabrication of the semiconductor elements. In order to detect undesired connections between conductive structures within the multiple layers on the semiconductor wafer, the prior art discloses a method of producing finger shaped layers
10 in the test structure comprising conductive layers reflecting the same distances and orientations with respect to one another as in the semiconductor elements to be produced. The conductive layers in the test structure are designed such that they can be easily connected to a test arrangement for supplying voltages to the conductive layer, in order to test undesired shorts between them. If the test structure shows an undesired electrical short, most probably
15 the semiconductor elements on the same semiconductor wafer will also show similar undesired shorts.

In nowadays 0.18 micron technology (and smaller), the test structure provided by this prior art document is not sufficient anymore. There is a need for an improved method
of detecting defects during production of CMOS 0.18 micron technology (and smaller).

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Therefore, the invention provides a method of producing at least one semiconductor element in a semiconductor substrate, the semiconductor element having a plurality of cell types, the method comprising:

- 25 - producing at least one test structure on the semiconductor substrate, comprising a predetermined number of test cells having cell types similar to one or more of the plurality of cell types
- each of the cell types having at least a first and second local interconnect layer structure, respectively, to be connected to predetermined supply voltages

during use, a plurality of first and second polysilicon layer structures, respectively, to provide control voltages to first and second electronic component structures, respectively;

- connecting in the test structure all of the plurality of the first polysilicon layer structures to one another to provide an interconnected first polysilicon layer structure, and connecting in the test structure all of the plurality of the second polysilicon layer structures to one another to provide an interconnected second polysilicon layer structure;
- providing predetermined test voltages to the first and second local interconnect layer structures, and to the interconnected first and second polysilicon layer structures, respectively;
- measuring currents resulting from the test voltages to identify production errors.

By interconnecting all of the first polysilicon layers structures to one another and interconnecting all the second polysilicon layers structures in the test structure to one another there are basically four conductive different structures in the test structure. By then providing different voltages of a predetermined value between those four conductive structures, several kinds of potential electrical shorts or leakage currents can be easily established. If the test structure shows such undesired shorts or leakage currents, it may be assumed that the semiconductor elements show these kinds of defects too.

Preferably, the test voltages are selected such that at least one of the following production errors may be determined:

- one or more electrical shorts between the first and second polysilicon layer structures;
- one or more electrical shorts between at least one of the first and second local interconnect layer structures and at least one of the first and second polysilicon layer structures;
- n-gate oxide leakages;
- p-gate oxide leakages.

The present invention also relates to a semiconductor substrate comprising at least one semiconductor element, the semiconductor element having a plurality of cell types, and at least one test structure comprising a predetermined number of test cells having cell types similar to one or more of the plurality of cell types, each of the cell types having at least a first and second local interconnect layer structure, respectively, to be connected to

predetermined supply voltages during use, a plurality of first and second polysilicon layer structures, respectively, to provide control voltages to first and second electronic component structures, respectively, in the test structure all of the plurality of the first polysilicon layer structures being connected to one another to provide an interconnected first polysilicon layer structure, and in the test structure all of the plurality of the second polysilicon layer structures being connected to one another to provide an interconnected second polysilicon layer structure.

Finally, the present invention relates to a semiconductor device comprising such a substrate.

The present invention will be illustrated with reference to some drawings which are only intended to explain the present invention but not to limit its scope, which is only limited by the scope of the annexed claims.

Figure 1 shows schematically a wafer and a plurality of reticles on the wafer during production of semiconductor elements;

Figure 2 shows schematically one of the reticles of figure 1;

Figure 3 shows schematically a blockdiagram of a test structure;

Figure 4 shows schematically a top view of a portion of a YEM cell in the test structure;

Figure 5a shows schematically a top view of a four transistor construction in the semiconductor element to be tested;

Figure 5b shows schematically a top view of a four transistor cell in the YEM structure used for testing the four transistor structure of figure 5a;

Figures 6a and 6b show equivalent electrical circuits of the structures shown in figures 5a and 5b, respectively;

Figure 7 shows a schematic lateral section of two transistors of the equivalent circuit of figure 6b.

Figure 1 shows very schematically a circular wafer 1 made of a semiconductor material, e.g., silicon or any other applicable semiconductor material known to persons skilled in the art. The wafer is, e.g., 200 mm in diameter.

During production of semiconductor elements on the wafer 1, a plurality of reticles 2 are produced on the wafer 1. There are, e.g., 50 of such reticles 2. The reticles 2, as is known to persons skilled in the art, may have the form of a square. Every reticle 2 comprises the same semiconductor elements. When the production of the semiconductor elements is ready, the reticles 2 are separated from one another by sawing, as is known to persons skilled in the art.

Figure 2 shows an example of a reticle 2. The reticle 2 comprises a plurality of semiconductor elements 4. Figure 2 shows two of such semiconductor elements 4, however, there may be present many more of such semiconductor elements 4. A saw line 7 shows where the reticle 2 will be separated from its neighbour's.

As is known to a person skilled in the art, the area 6 where the reticle 2 is separated from its neighbour's, may be provided with very small product characterisation modules PCM. These PCM's comprise test structures providing a limited possibility of characterising the process to produce the semiconductor elements 4.

The reticle 2 may also comprise one or more process evaluation modules PEM 3. Such PEM's 3 are also known from the prior art and are used to measure process parameters as well as the data used for process development.

The reticle 2 also comprises at least one yield evaluation module YEM 5. Also, YEM's are known from the prior art and are used for purposes of yield verification. A limited number of these YEM's is available in view of the limited reticle surface of, e.g., 4 cm².

The present invention relates to a modified YEM structure used for testing.

Figure 3 shows how the YEM 5 may be designed in accordance with the invention. The YEM 5, e.g., comprises 16 different cell structures 5 (1), ... 5 (16). Each of the cells 5 (i), i = 1, ... 16, comprises a plurality of semiconductor elements with similar structure as the semiconductor elements 4 to be tested. Figure 3 shows that these cells 5 (i) are arranged in 8 columns and 2 rows. However, there may be provided other numbers of cells in other arrangements.

It has been found, that, in most cases, a limited number of cells (e.g. 16 as in the example of figure 3) may already be representative of a very large number of the electrical components in the semiconductor elements 4. For instance, the table below shows that 16 cells with the highest number of electrical components in a DSP block (DSP = Digital Signal Processing) in the semiconductor elements 4 may cover about 70% of the total area covered by the DSP block in the semiconductor element 4. Therefore, designing the YEM 5 with 16 cells with similar electronic components as in the semiconductor element 4 results in

having a test structure representative of the majority of electronic components in the semiconductor elements 4.

	cell	#	function
1	nd2	3508	input NAND
2	rdmr_fdlsqx2	2290	flip flop
3	iv	2057	inverter
4	ao2	1777	input BOOLEAN
5	ao3a	1207	input BOOLEAN
6	gate_decap9	1158	decoupling cell
7	mux21	1021	input MUX
8	nd3	927	input NAND
9	nr2	905	input NOR
10	nd2a	575	input NAND
11	ao7a	551	input BOOLEAN
12	en2	479	input OBSOLETE
13	ao2n	448	input BOOLEAN
14	bfltx2	428	plain BUFFER
15	a06	344	input BOOLEAN
16	eo2	332	input OBSOLETE
	eo2		
	total added area	0.462 mm2	
	total area dsp	0.666 mm2	
	covered	69.4%	

Figure 4 shows a top view of an example YEM cell portion in accordance with the invention. The YEM structure comprises a plurality of electrical components that are

interconnected in a predetermined way in order to be able to perform the desired electrical tests.

Figure 4 shows four metal lines/connections 16 (1), 16 (2), 16 (3), 16 (4) of a same metal layer on top of the cell structure. Below the metal lines 16 (1)... 16 (4), there are provided several local interconnection layer (LIL) structures 10. Usually these local interconnection layers are made of polysilicon, polysilicon having a silicide layer on top of it, or metal, as is known to a person skilled in the art.

In a layer below the metal lines 16 (1), ... 16 (4), there are provided polysilicon layers 12, usually, to connect gates of transistors to control voltages to control the operation of the transistors. In the present structure, there are at least 2 sets of different polysilicon layers where portions of the one set are not allowed to show electrical shorts to portions of the other one.

The test structure also comprises source and drain regions 18.

Electrical contacts between the metal lines 16 (1), ... 16 (4) and underlying polysilicon layers 12 and LIL 10 are indicated with reference numbers 14.

The structure of the YEM cell is similar to, but not equal to the associated cell structures used in the semiconductor elements 4. This will be further explained with reference to figures 5a and 5b. In accordance with the invention, in the YEM structure, the polysilicon structure 12, the LIL structure 10, as well as the source and drain 18 are equal to the respective same areas in the original electrical components in the semiconductor elements 4. Only the metal lines 16 (1), 16 (4) and their connections to the underlying structures have been amended to provide for an easy test environment.

Figure 5a shows an original four transistor cell of a semiconductor element 4. Figure 5b shows a portion of figure 4 on an enlarged scale and reflects how the original structure of figure 5a is modified in the YEM cell. The same reference numbers as in figure 4 refer to the same areas. So, figure 5a shows a structure of which potential production errors will be identified not by testing the structure of figure 5a itself but by testing the structure of 5b that has been changed relative to figure 5a as further explained below. Figure 5a shows that the original structure comprises other metal lines, here indentified with 15(1), ...15(5), than the modified structure of figure 5b. E.g., in figure 5a, metal line 15(5) is connected to a LIL 10(2) (and normally also to ground), whereas in figure 5b, the corresponding metal line 16(4) is additionally connected to a drain of one of the transistors. Also the other metal lines 15(1), ...15(4) have other areas and connections than corresponding metal lines 16(1), ...16(3) in figure 5b. E.g., metal line 15(1) in figure 5a is connected both to a LIL 10(1) and a

source/drain area 18 whereas in figure 5b, metal line 16(1) is only connected to the LIL 10(1).

The metal line 16 (1) is to be connected to a first power supply voltage, whereas the metal line 16 (4) is to be connected to a second power supply voltage.

5 Figures 5a and 5b show that in the four transistor cell arrangement there are two different polysilicon lines 12 (1), 12 (2). Regions 18(1) and 18(2) define source and drain regions for the four transistors.

10 Metal line 16 (2) is used to interconnect all polysilicon layer structures 12 (2) in the entire cell, and the metal line 16 (3) is used to interconnect all polysilicon layer structures 12 (1) in the entire cell.

Figure 6a shows an equivalent electronic circuit of the structure shown in figure 5a. It comprises four transistors T1, T2, T3, T4. All the transistors are MOS transistors. Transistors T1 and T2 are PMOS transistors, whereas transistors T3 and T4 are NMOST transistors. The transistors T1, T2 have sources connected to a power supply line Vdd, e.g., 1.8V. The drains of the transistors T1, T2 are connected to one another and provide an output Outp Z.

The drains of the transistors T1, T2 are also connected to a source of transistor T3. Transistor T3 has its drain D connected to source S of transistor T4. Transistor T4 has its drain D connected to power supply voltage Vss, e.g., being on ground level 0V.

20 Transistors T1, T3 have gates connected to a common input line Inp A. Transistors T2, T4 have gates connected to an input line Inp B.

Figure 6b shows an equivalence circuit of the structure shown in figure 5b. It also shows a four transistor cell, however, arranged in a slightly different way than the structure of figure 6a. Figure 6b shows that the four transistor cell is arranged as two CMOS structures. Transistors T5, T6 are arranged as a first CMOS structure having gates connected together to the polysilicon line 12 (1), also indicated in figure 6b with "pol1".

Transistors T7, T8 are arranged as a second CMOS structure having their gates connected to a second polysilicon line 12 (2), in figure 6b also indicated with "pol2".

30 Moreover figure 6b shows how the areas 16 (1), 16 (4), 18 (1), 18 (2) correspond to electrical connections of the equivalent electronic circuit.

Although the equivalent electronic circuit of figure 6b differs from the electronic circuit of the electronic components in the semiconductor elements 4, as shown in figures 6a, the basic structures of LIL 10, polysilicon 12, and source and drain regions 18 do have the same relative locations in the YEM structure. Only the way they are interconnected

in the YEM structure by the metal lines 16 (1), ... 16 (4) differs such that an easy test measurement can be performed.

The arrangement of figure 5b allows for instance to made the following test measurements in the YEM structure, as indicated in the table below.

	pol1	pol2	li1	li2
	[V]	[V]	[V]	[V]
polpol shorts	0	1.8	1.8	0
polLIL shorts	0	0	1.8	1.8
Nmost leakage	1.8	1.8	1.8	0
Pmost leakage	0	0	1.8	0

Where:

polpol shorts = electrical shorts between pol1 and pol2 structures in the YEM structure;

polLIL shorts = electrical shorts between one or more of the pol1 and pol2 structures and one or more of the LIL and LIL1 and LIL2 structures (cf. figure 6b);

Nmost leakage = leakage currents through the Nmost T6, T8 (cf. figure 6b);

Pmost leakage = leakage currents in Pmost T5, T7 (cf. figure 6b).

After applying the voltages as indicated in the table above, no currents may be detected when the structures are located correctly. If currents (above a predetermined threshold level) are detected, one or more of the errors indicated above are present. If these errors are present in the YEM structure, one can conclude that, most probably, similar defects are present in the semiconductor elements 4 in the same reticle 2.

Figure 7, finally, shows a schematic lateral view of transistors T5 and T6 of the circuit shown in figures 5b and 6b. The transistor T5 is connected with its source 26 to li1 line 10 via a contact 36. Transistor T5 comprises a gate 27 separated from an Nwell 22 by means of an insulating layer (not shown). Transistor T5 comprises a drain 28.

Transistor T5 also comprises an N+ region 24 connected to li1 line 10 via a contact 38 for providing the Nwell 22 with an appropriate bias voltage.

Transistor T6 is arranged directly in a P substrate 20 and is provided with a drain 30, a source 32 and a gate 31. The source 32 is connected to li2 line 10 via a contact

40. Transistor T6 comprises a P+ region 34 connected to lil2 line 10 via a contact 42 for providing the substrate with a proper bias voltage.

The gates 27, 31 of the transistors T5, T6 are interconnected by polysilicon line 12 (1) (poll).

5 Although the present invention has been illustrated with reference to a four transistor structure (figures 5a and figures 5b), and especially with a CMOS structure as a test structure (figures 5b and 6b), the present invention is not limited to these types of electrical components in the cell structures. Other cell types and electrical components in the semiconductor elements 4 and in the YEM structure may be provided.

10 Moreover, the present invention is in no way limited to the doping types given in, e.g., figure 7. Other dopings may be provided, if necessary.

CLAIMS:

20 12. 2002

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1. Method of producing at least one semiconductor element in a semiconductor substrate, the semiconductor element having a plurality of cell types, the method comprising:

- producing at least one test structure on said semiconductor substrate, comprising a predetermined number of test cells having cell types similar to one or more of said plurality of cell types;
- each of said cell types having at least a first and second local interconnect layer structure, respectively, to be connected to predetermined supply voltages during use, a plurality of first and second polysilicon layer structures, respectively, to provide control voltages to first and second electronic component structures, respectively;
- connecting in said test structure all of said plurality of said first polysilicon layer structures to one another to provide an interconnected first polysilicon layer structure, and connecting in said test structure all of said plurality of said second polysilicon layer structures to one another to provide an interconnected second polysilicon layer structure;
- providing predetermined test voltages to said first and second local interconnect layer structures, and to said interconnected first and second polysilicon layer structures, respectively;
- measuring currents resulting from said test voltages to identify production errors.

2. Method according to claim 1, wherein said plurality of said first and second polysilicon layer structures, respectively, are interconnected to one another, respectively, using metal connection structures.

3. Method according to claim 1 or 2, wherein said test structure comprises CMOS transistors.

4. Method according to any of the preceding claims, wherein said test voltages are selected such that at least one of the following production errors may be determined:

- one or more electrical shorts between said first and second polysilicon layer structures;
- 5 - one or more electrical shorts between at least one of said first and second local interconnect layer structures and at least one of said first and second polysilicon layer structures;
- n-gate oxide leakages;
- p-gate oxide leakages.

10 5. Method according to any of the preceding claims, wherein said at least one semiconductor element is located in one of a plurality of reticles on a semiconductor wafer.

15 6. A semiconductor substrate comprising at least one semiconductor element, the semiconductor element having a plurality of cell types, and at least one test structure comprising a predetermined number of test cells having cell types similar to one or more of said plurality of cell types, each of said cell types having at least a first and second local interconnect layer structure, respectively, to be connected to predetermined supply voltages during use, a plurality of first and second polysilicon layer structures, respectively, to provide
20 control voltages to first and second electronic component structures, respectively, in said test structure all of said plurality of said first polysilicon layer structures being connected to one another to provide an interconnected first polysilicon layer structure, and in said test structure all of said plurality of said second polysilicon layer structures being connected to one another to provide an interconnected second polysilicon layer structure.

25 7. A semiconductor device comprising a substrate according to claim 6.

ABSTRACT:

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(68)

Testing production of semiconductor elements on a substrate, the semiconductor element having a plurality of cell types, by providing at least one test structure on the substrate with a number of test cells having cell types similar to one or more of the plurality of cell types, each of the cell types having at least a first and second local

5 interconnect layer structure, respectively, to be connected to predetermined supply voltages during use, a plurality of first and second polysilicon layer structures, respectively, to provide control voltages to first and second electronic component structures, respectively, connecting in the test structure all of the plurality of the first polysilicon layer structures to one another to provide an interconnected first polysilicon layer structure, and connecting in the test

10 structure all of the plurality of the second polysilicon layer structures to one another to provide an interconnected second polysilicon layer structure, providing predetermined test voltages and measuring currents resulting from the test voltages to identify production errors.

Fig. 2

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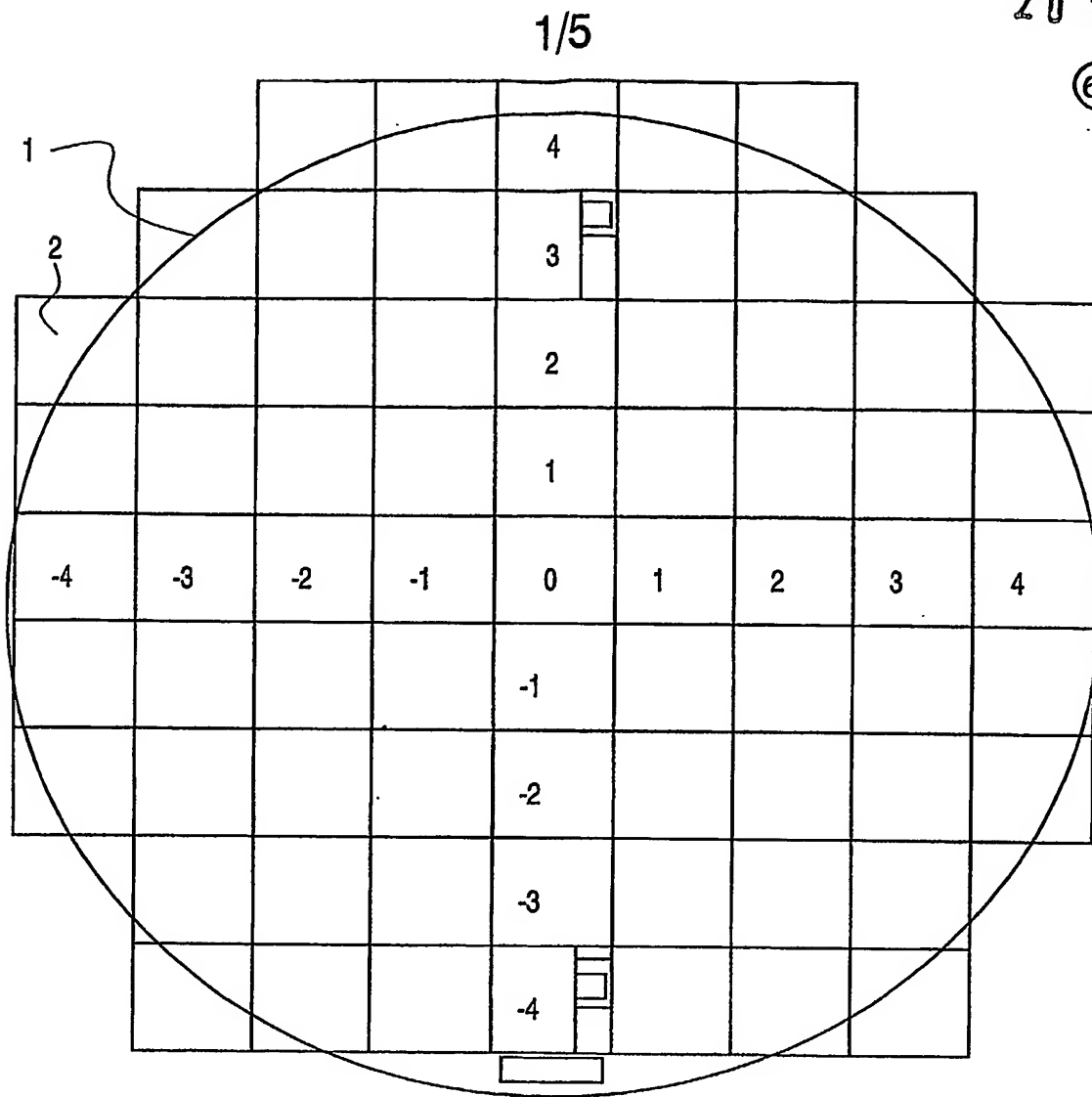


FIG. 1

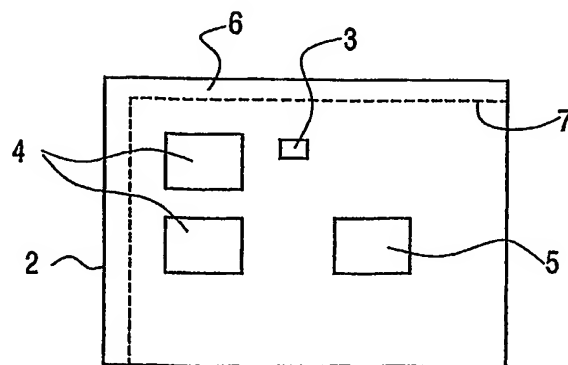


FIG. 2

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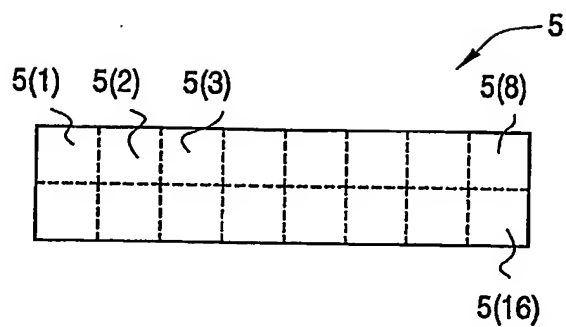


FIG. 3

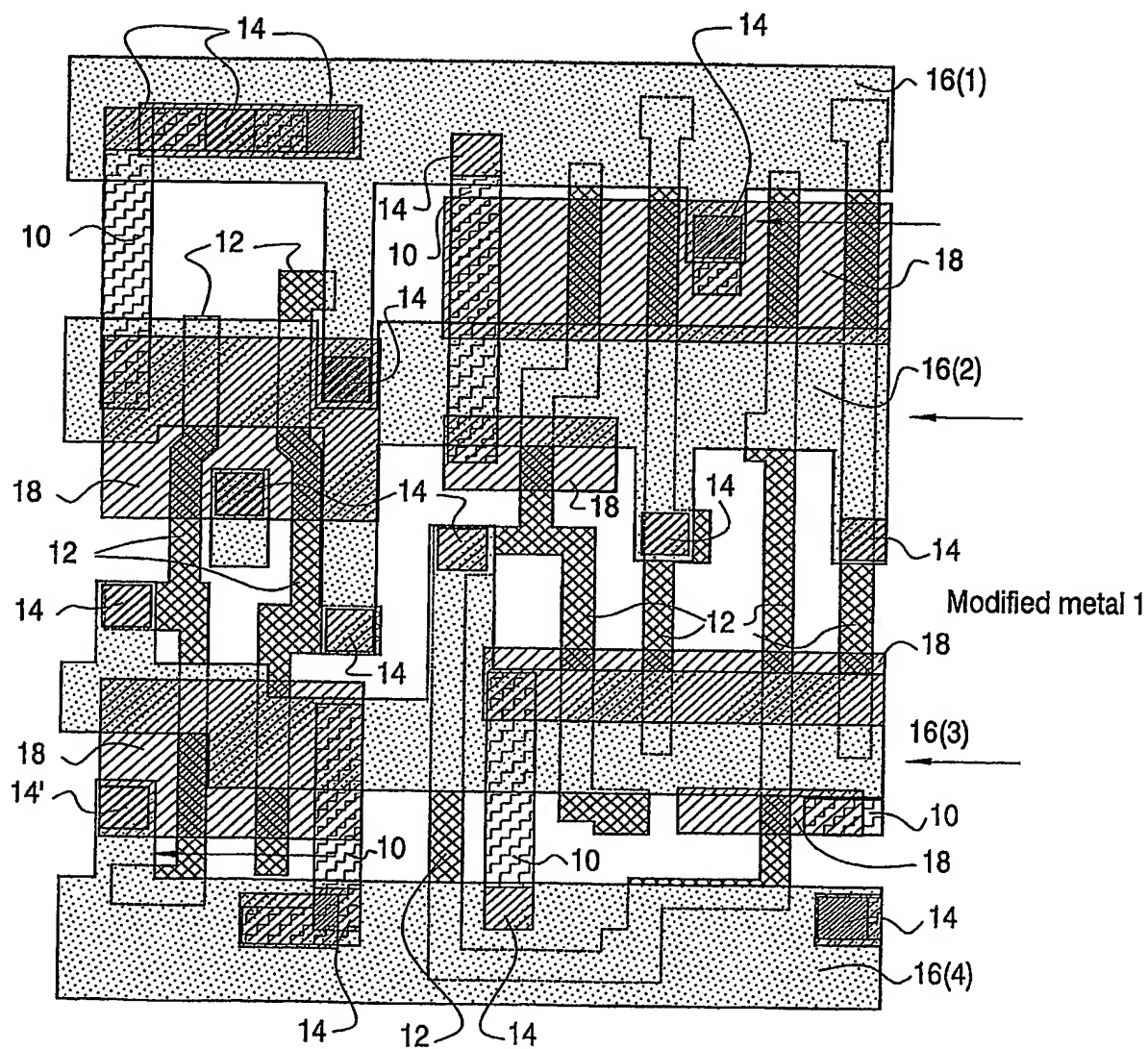


FIG. 4

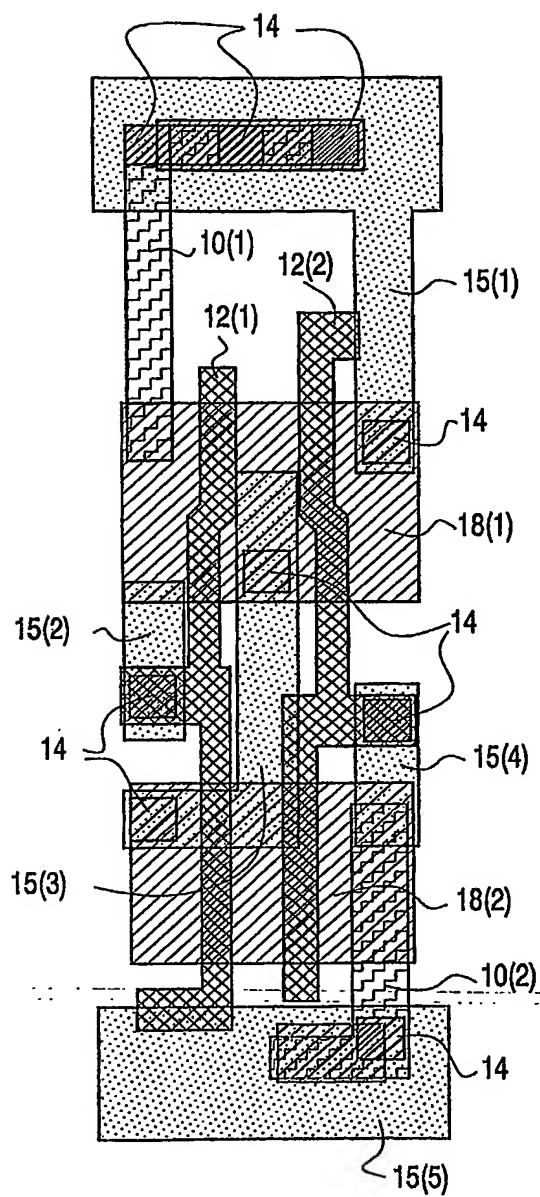


FIG. 5a

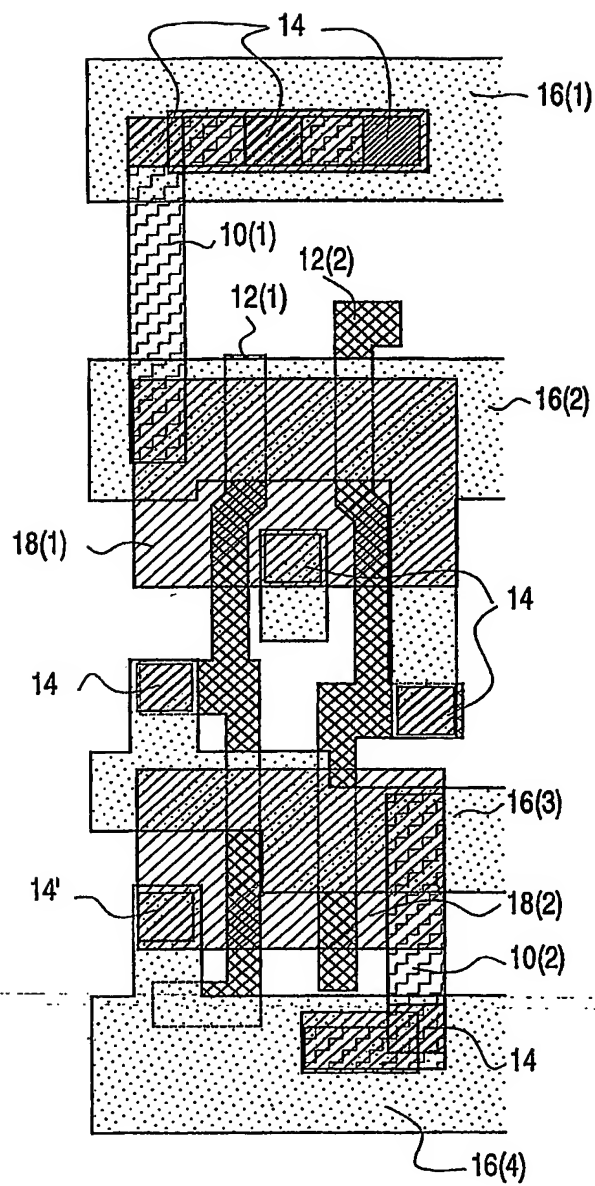


FIG. 5b

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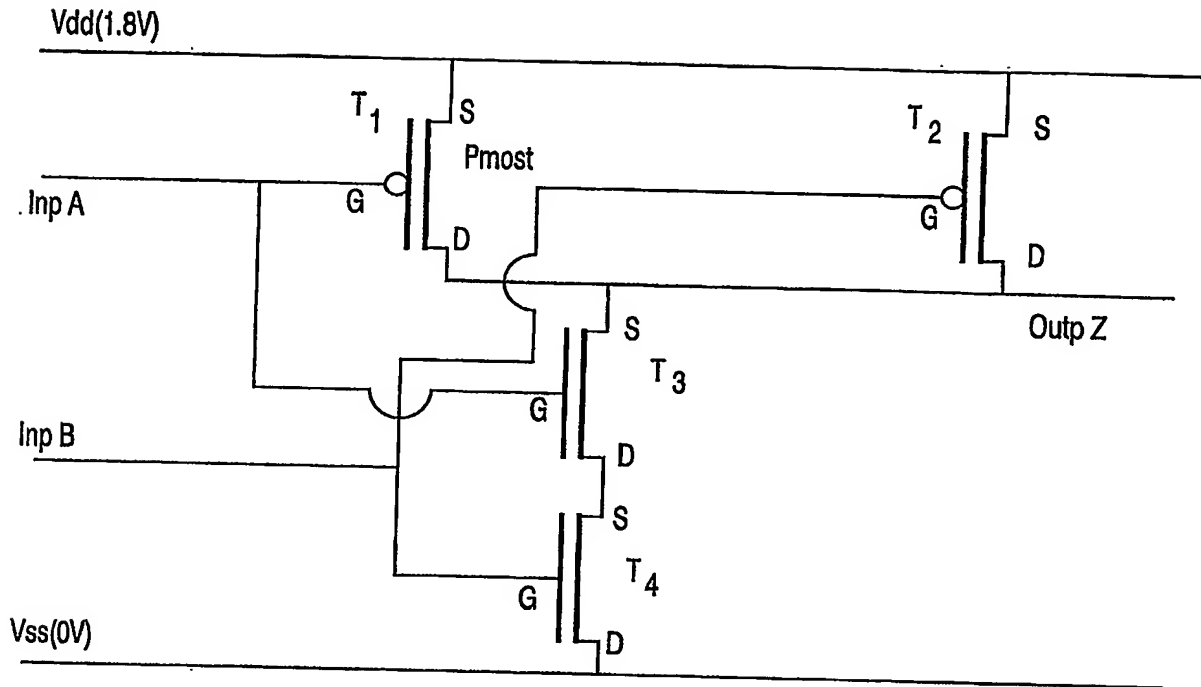


FIG. 6a

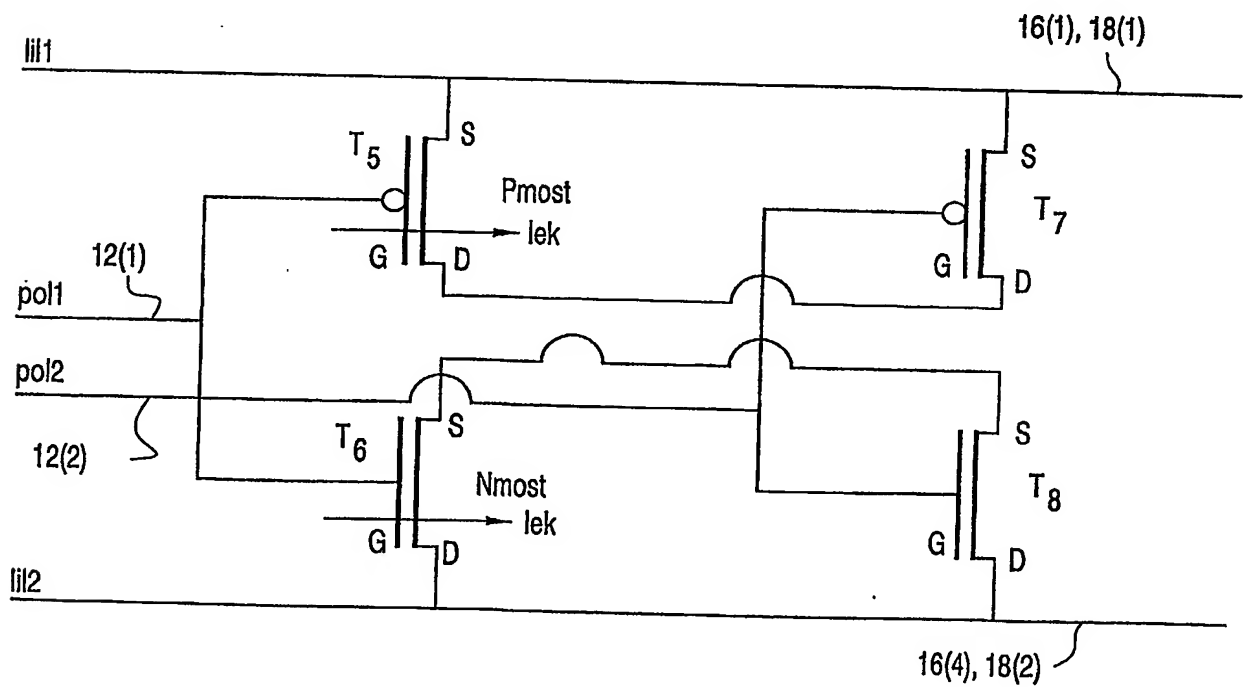


FIG. 6b

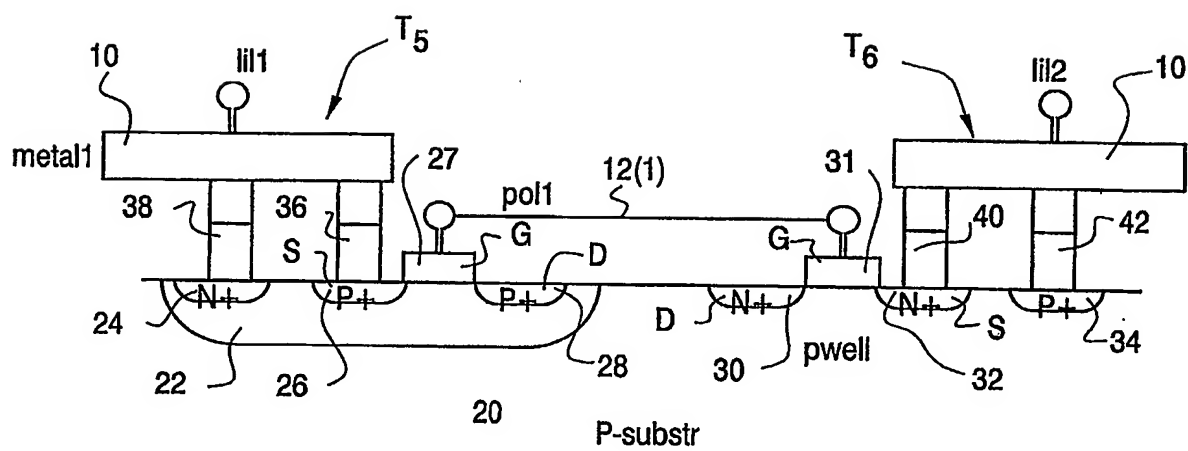


FIG. 7